



(19)

Generated Document.

(11) Publication number: 05062911 A

## PATENT ABSTRACTS OF JAPAN

(21) Application number: 03223234

(22) Application date: 04.09.91

(51) Intl. Cl.: H01L 21/205 H01S 3/18

(30) Priority:

(43) Date of application 12.03.93  
publication:(84) Designated contracting  
states:

(71) Applicant: FUJITSU LTD

(72) Inventor: NAKAI KENYA

(74) Representative:

(54) MANUFACTURE OF  
SEMICONDUCTOR  
SUPERLATTICE

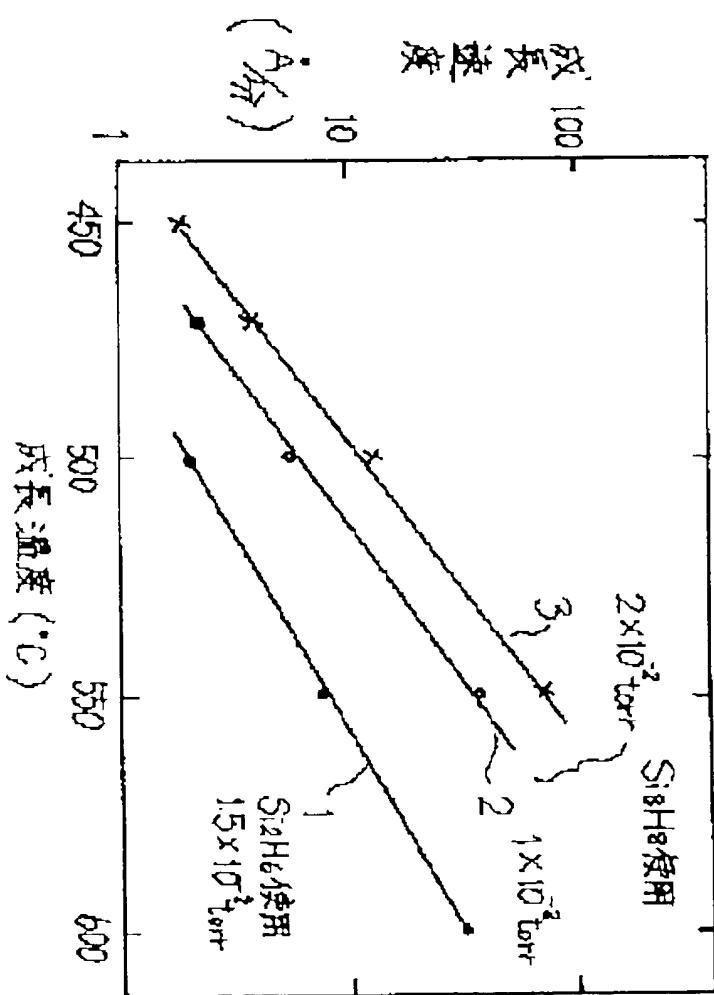
(57) Abstract:

PURPOSE: To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

CONSTITUTION: The title semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH<sub>4</sub> and trisilane (Si<sub>3</sub>H<sub>8</sub>) as raw gas and also using H<sub>2</sub> or inert gas as carrier gas.

COPYRIGHT: (C)1993,JPO&Iapio



05062911 A

1 455 - 4 01 4